



ABSTRACT

A pretreating process for exhaust gas produced in a semiconductor or liquid crystal module production device such as a film forming device, wherein a maintenance work is restricted or safety of the work is improved. A pretreating
5 method for a film-forming exhaust gas containing Si components, comprising the steps of burning and treating an exhaust gas, dedusting Si-containing dust from a combustion exhaust gas produced in the burning step. cleaning by water the dedusted combustion exhaust gas. This method that removes Si-containing dust in
10 the dedusting process can restrict the precipitation of precipitators during the cleaning step, whereby ensuring a stable treating process, alleviating maintenance work, and conducting a cleaning process without requiring a large amount of cleaning water.

15

20

25